

## N-Channel Enhancement Mode Power MOSFET

### Description

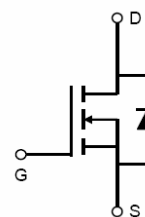
The HM2302B uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

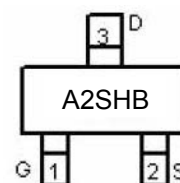
- $V_{DS} = 20V, I_D = 2.5A$   
 $R_{DS(ON)} < 60m\Omega @ V_{GS}=2.5V$   
 $R_{DS(ON)} < 45m\Omega @ V_{GS}=4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

### Application

- Battery protection
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
A2SHB	HM2302B	SOT-23	Ø180mm	8 mm	3000 units

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	2.5	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	10	A
Maximum Power Dissipation	$P_D$	0.9	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ\text{C}$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	139	$^\circ\text{C/W}$
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### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$	-	-	1	$\mu A$

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.75	1.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=2.8A$	-	35	60	m $\Omega$
		$V_{GS}=4.5V, I_D=3A$	-	29	45	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=3A$	-	8	-	S
<b>Dynamic Characteristics</b> (Note4)						
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	260	-	PF
Output Capacitance	$C_{oss}$		-	48	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	27	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=3.3\Omega$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	2.5	-	nS
Turn-on Rise Time	$t_r$		-	3.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	21	-	nS
Turn-Off Fall Time	$t_f$		-	3	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=3A,$ $V_{GS}=4.5V$	-	2.9	5	nC
Gate-Source Charge	$Q_{gs}$		-	0.4	-	nC
Gate-Drain Charge	$Q_{gd}$		-	0.6	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=2.5A$	-	0.75	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	2.5	A

## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

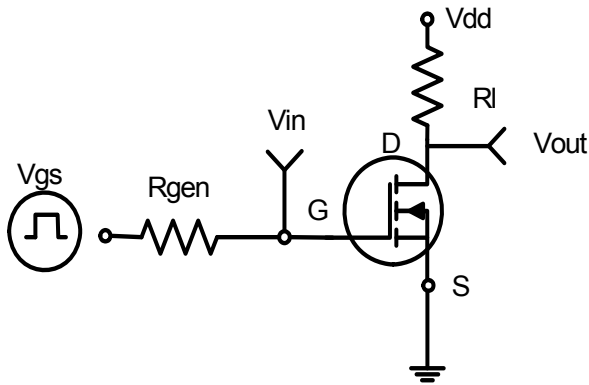


Figure 1: Switching Test Circuit

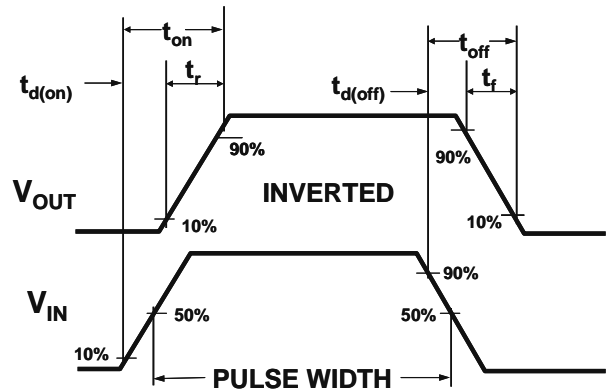
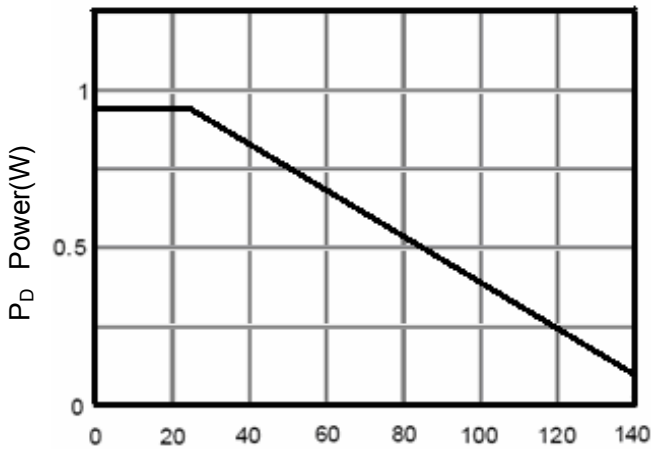
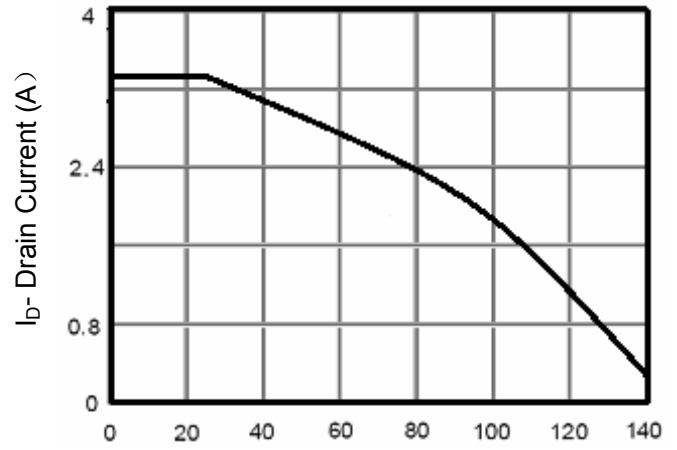


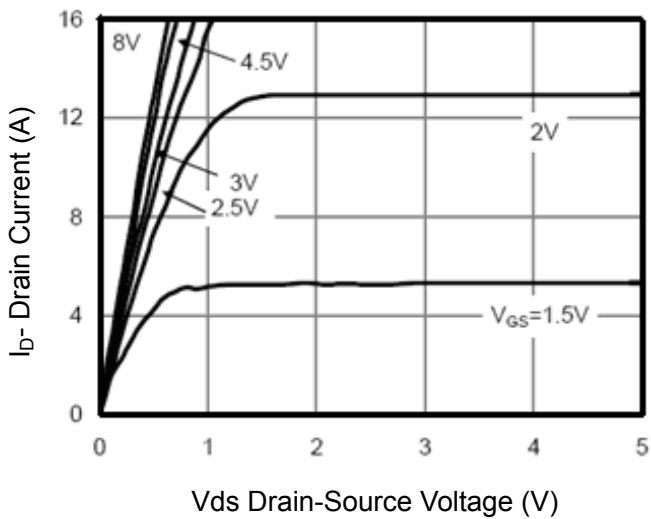
Figure 2: Switching Waveforms



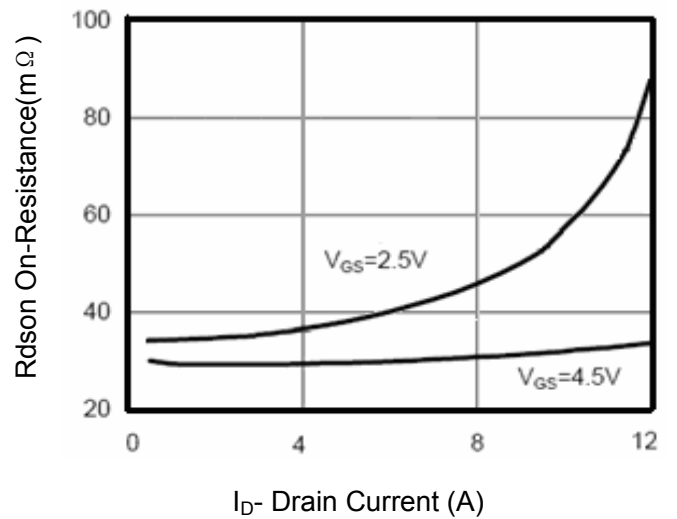
T<sub>J</sub>-Junction Temperature(°C)  
 Figure 3 Power Dissipation



T<sub>J</sub>-Junction Temperature(°C)  
 Figure 4 Drain Current



V<sub>DS</sub> Drain-Source Voltage (V)  
 Figure 5 Output Characteristics



I<sub>D</sub>- Drain Current (A)  
 Figure 6 Drain-Source On-Resistance

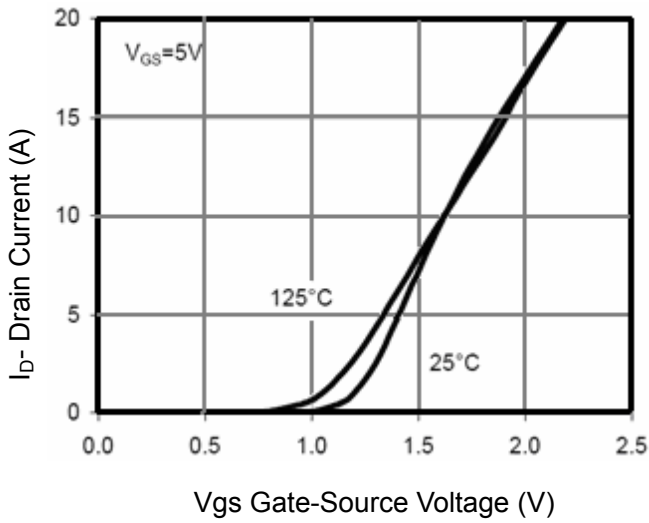


Figure 7 Transfer Characteristics

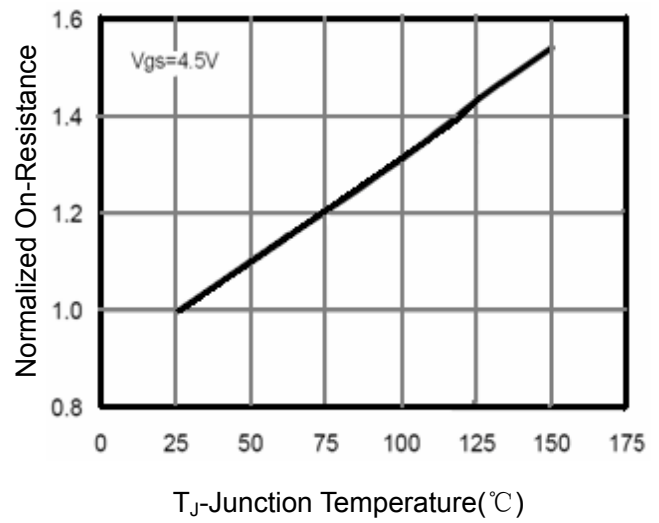


Figure 8 Drain-Source On-Resistance

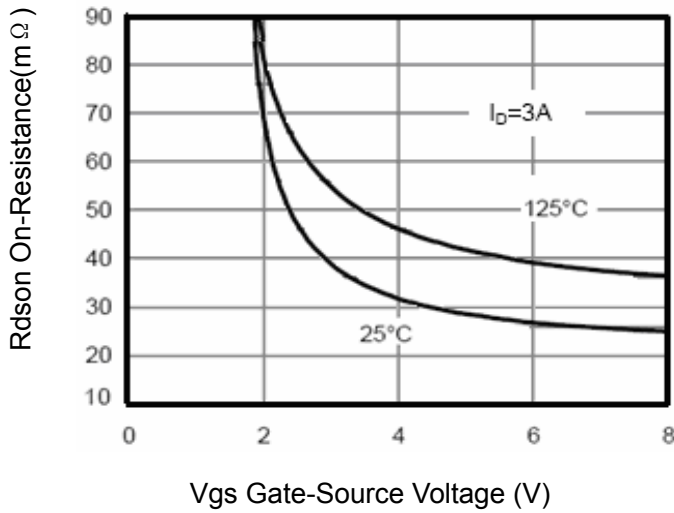


Figure 9  $R_{DS(on)}$  vs  $V_{GS}$

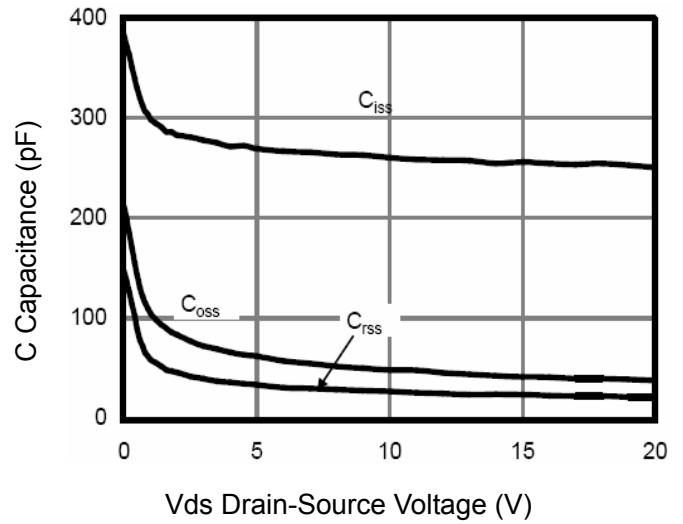


Figure 10 Capacitance vs  $V_{DS}$

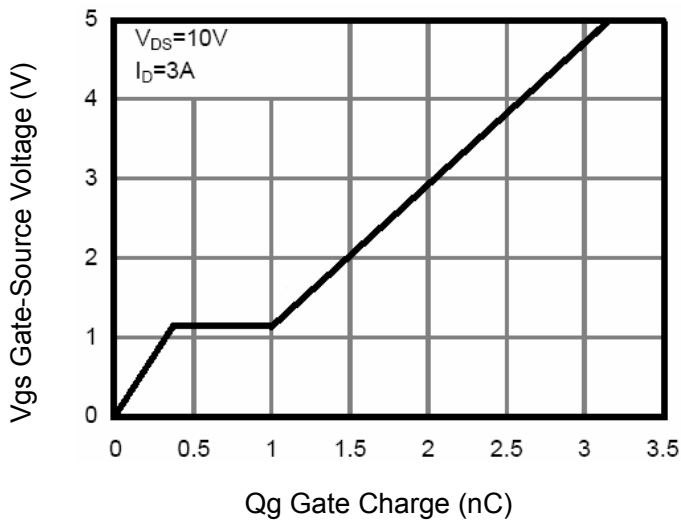


Figure 11 Gate Charge

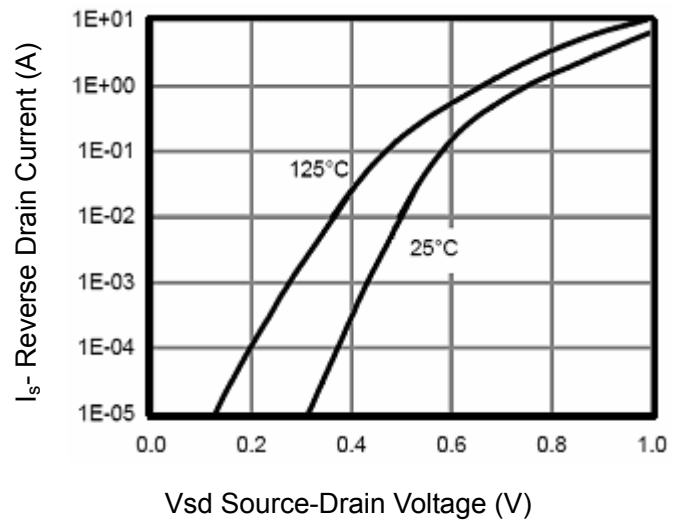
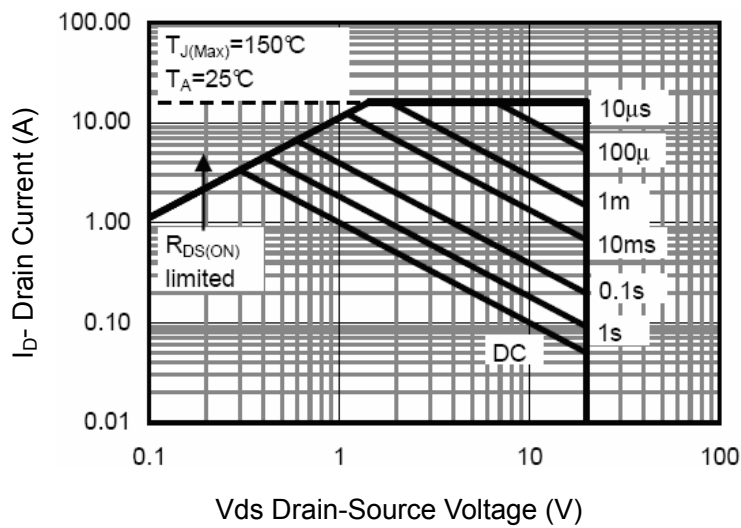
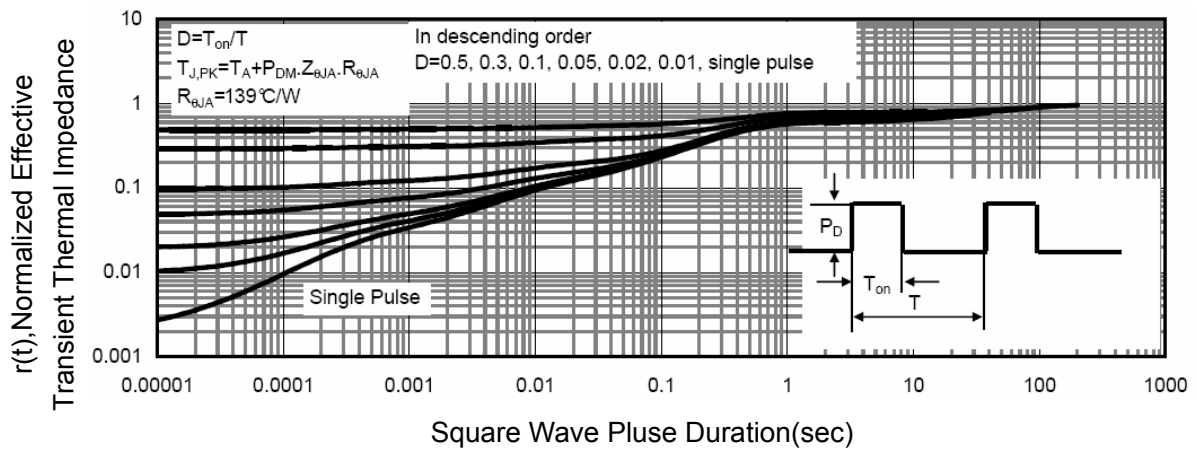


Figure 12 Source- Drain Diode Forward

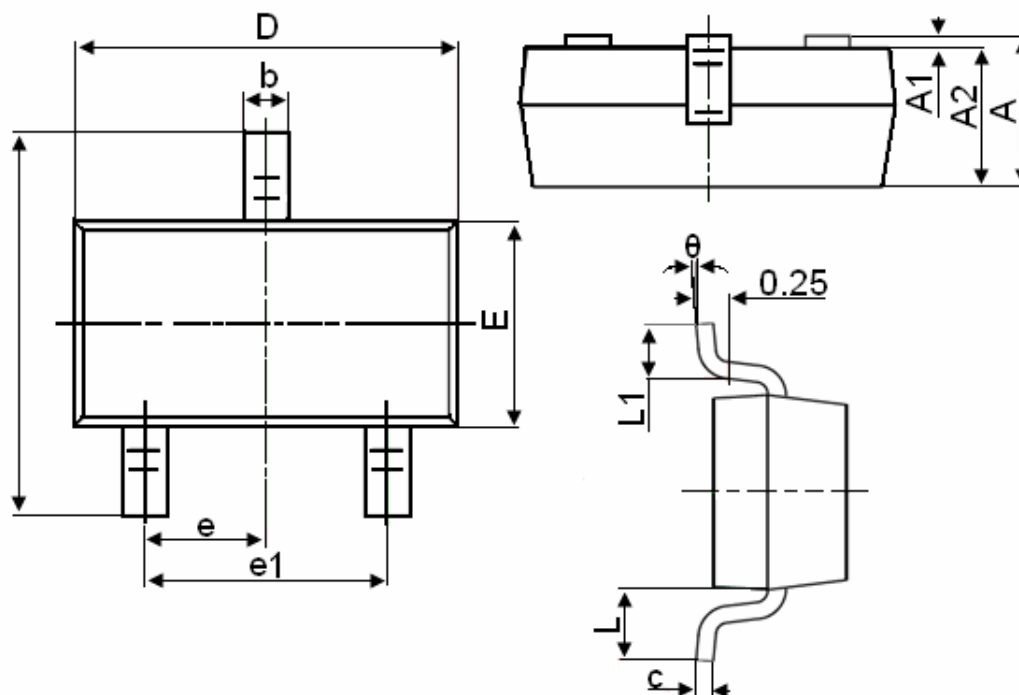


**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Notes

1. All dimensions are in millimeters.
2. Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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